

## N-Channel 100-V (D-S) MOSFET

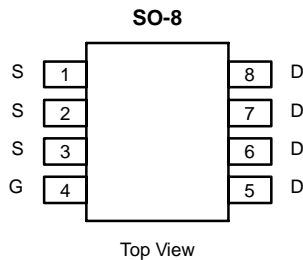
PRODUCT SUMMARY		
$V_{DS}$ (V)	$r_{DS(on)}$ ( $\Omega$ )	$I_D$ (A)
100	0.025 @ $V_{GS} = 10$ V	7.7
	0.031 @ $V_{GS} = 6.0$ V	6.9

### FEATURES

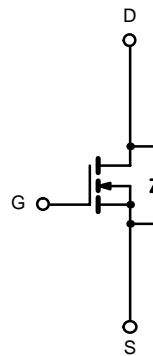
- TrenchFET® Power MOSFET
- Low Gate Charge

### APPLICATIONS

- Primary Side Switch



Ordering Information: Si4496DY  
Si4496DY-T1 (with Tape and Reel)



ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)					
Parameter		Symbol	10 secs	Steady State	Unit
Drain-Source Voltage		$V_{DS}$	100		V
Gate-Source Voltage		$V_{GS}$	$\pm 20$		
Continuous Drain Current ( $T_J = 150^\circ\text{C}$ ) <sup>a</sup>	$T_A = 25^\circ\text{C}$	$I_D$	7.7	4.6	A
	$T_A = 70^\circ\text{C}$		6.2	4.1	
Pulsed Drain Current		$I_{DM}$	30		
Single Avalanch Current	L = 0.1 mH	$I_{AS}$	35		
Single Avalanch Energy		$E_{AS}$	61		mJ
Continuous Source Current (Diode Conduction) <sup>a</sup>		$I_S$	2.6	1.2	A
Maximum Power Dissipation <sup>a</sup>	$T_A = 25^\circ\text{C}$	$P_D$	3.1	1.4	W
	$T_A = 70^\circ\text{C}$		2.0	0.9	
Operating Junction and Storage Temperature Range		$T_J, T_{stg}$	-55 to 150		$^\circ\text{C}$

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient <sup>a</sup>	t $\leq$ 10 sec	$R_{thJA}$	33	40	$^\circ\text{C/W}$
	Steady State		73	90	
Maximum Junction-to-Foot (Drain)	Steady State	$R_{thJF}$	15	18	

Notes

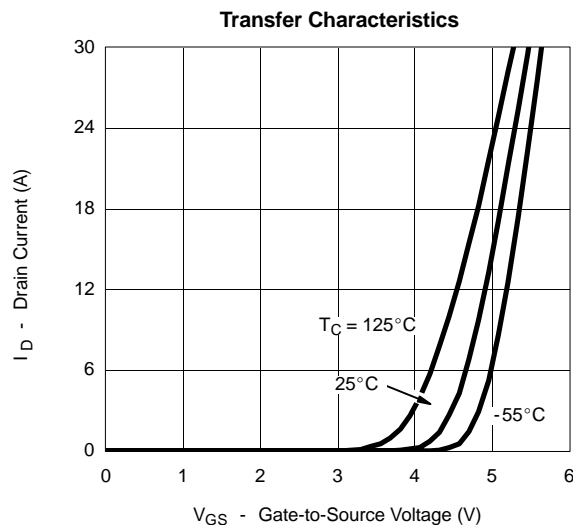
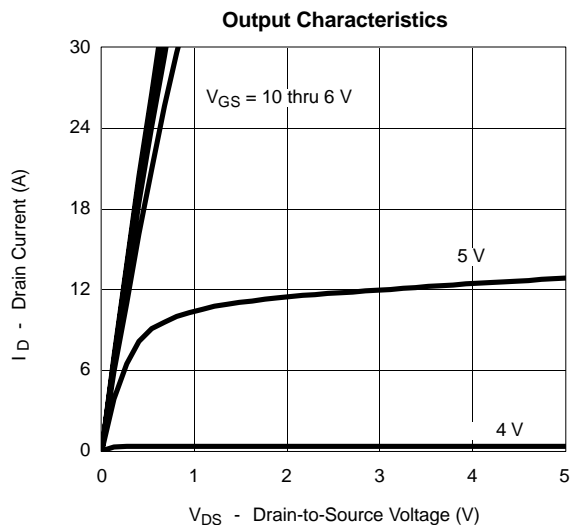
a. Surface Mounted on 1" x 1" FR4 Board.

**SPECIFICATIONS (T<sub>J</sub> = 25 °C UNLESS OTHERWISE NOTED)**

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
<b>Static</b>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA	2.0			V
Linear Threshold Voltage	V <sub>T</sub>			4.4		V
Gate-Body Leakage	I <sub>GSS</sub>	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ±20 V			±100	nA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 80 V, V <sub>GS</sub> = 0 V			1	μA
		V <sub>DS</sub> = 80 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 55 °C			5	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> ≥ 5 V, V <sub>GS</sub> = 10 V	30			A
Drain-Source On-State Resistance <sup>a</sup>	r <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 7.7 A		0.021	0.025	Ω
		V <sub>GS</sub> = 6.0 V, I <sub>D</sub> = 6.9 A		0.025	0.031	
Forward Transconductance <sup>a</sup>	g <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 7.7 A		23		S
Diode Forward Voltage <sup>a</sup>	V <sub>SD</sub>	I <sub>S</sub> = 2.6 A, V <sub>GS</sub> = 0 V		0.75	1.2	V
<b>Dynamic<sup>b</sup></b>						
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> = 50 V, V <sub>GS</sub> = 10 V, I <sub>D</sub> = 7.7 A		29	36	nC
Gate-Source Charge	Q <sub>gs</sub>			9.9		
Gate-Drain Charge	Q <sub>gd</sub>			10.3		
Gate Resistance	R <sub>G</sub>		0.5	1.2	1.9	Ω
Turn-On Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> = 50 V, R <sub>L</sub> = 50 Ω I <sub>D</sub> ≅ 1.0 A, V <sub>GEN</sub> = 10 V, R <sub>G</sub> = 6 Ω		17	26	ns
Rise Time	t <sub>r</sub>			13	20	
Turn-Off Delay Time	t <sub>d(off)</sub>			36	54	
Fall Time	t <sub>f</sub>			26	40	
Source-Drain Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 2.6 A, di/dt = 100 A/μs		45	68	

## Notes

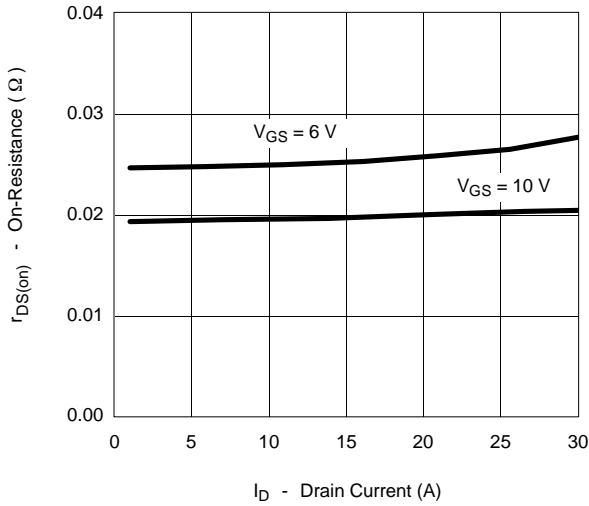
- a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%.  
b. Guaranteed by design, not subject to production testing.

**TYPICAL CHARACTERISTICS (25 °C UNLESS NOTED)**

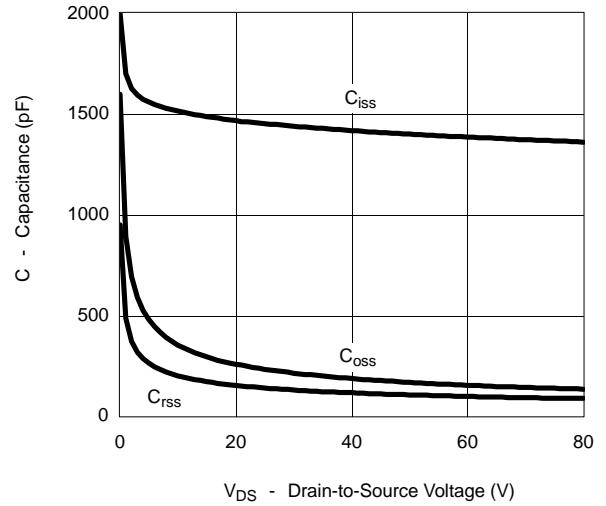


**TYPICAL CHARACTERISTICS (25 °C UNLESS NOTED)**

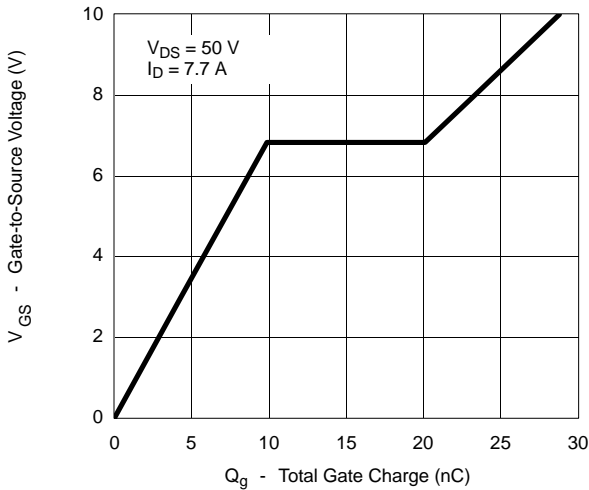
**On-Resistance vs. Drain Current**



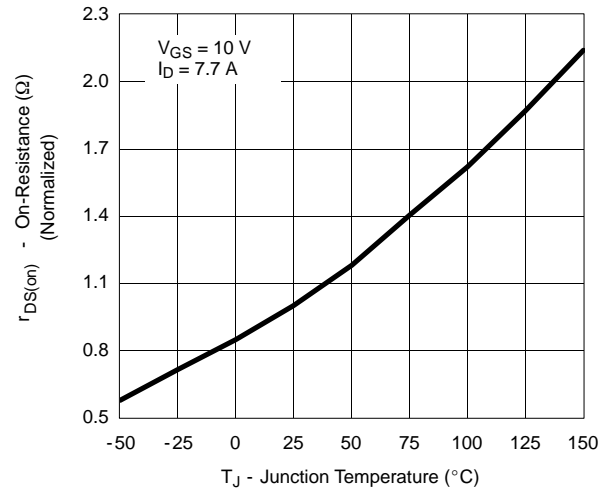
**Capacitance**



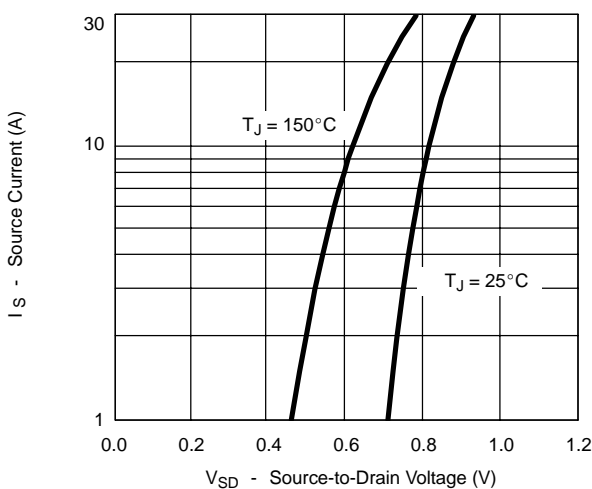
**Gate Charge**



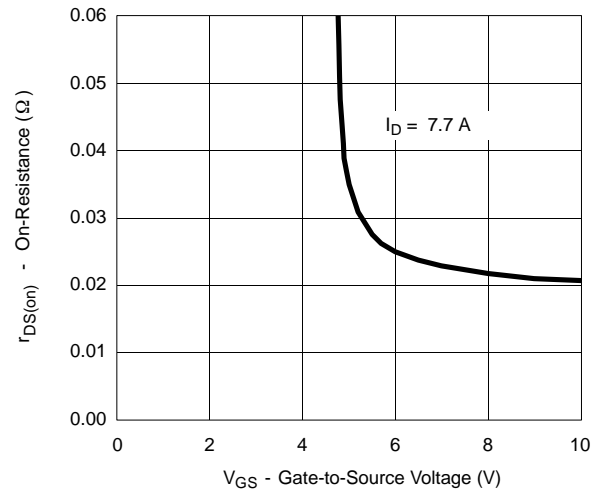
**On-Resistance vs. Junction Temperature**



**Source-Drain Diode Forward Voltage**



**On-Resistance vs. Gate-to-Source Voltage**



**TYPICAL CHARACTERISTICS (25 °C UNLESS NOTED)**

